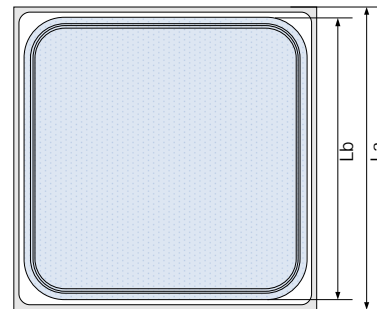


**2SB108100MA LOW IR SCHOTTKY BARRIER DIODE CHIPS**
**DESCRIPTION**

- Ø 2SB108100MA is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Due to special schottky barrier structure, the chips have very low reverse leakage current ( typical  $I_R=0.002\text{mA}@ V_r=100\text{V}$  ) and maximum 150°C operation junction temperature;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- Ø Chip Size: 1080 $\mu\text{m}$  X 1080 $\mu\text{m}$ ;
- Ø Chip Thickness: 280 $\pm$ 20 $\mu\text{m}$ ;


**Chip Topography and Dimensions**

 La: Chip Size: 1080 $\mu\text{m}$ ;

 Lb: Pad Size: 985 $\mu\text{m}$ ;

**ORDERING SPECIFICATIONS**

Product Name	Specification
2SB108100MAYY	For Axial leads package

**ABSOLUTE MAXIMUM RATINGS**

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	100	V
Average Forward Rectified Current	IFAV	2	A
Peak Forward Surge Current@8.3ms	IFSM	50	A
Maximum Operation Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-40~150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C)**

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=1mA	100	--	V
Forward Voltage	VF	IF=2A	--	0.85	V
Reverse Current	IR	VR=100V	--	1	mA